

Silicon PNP Power Transistors

2SA968 2SA968A 2SA968B

DESCRIPTION

- With TO-220 package
- Complement to type 2SC2238
- High breakdown votage

APPLICATIONS

- Power amplifier applications
- Driver stage amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

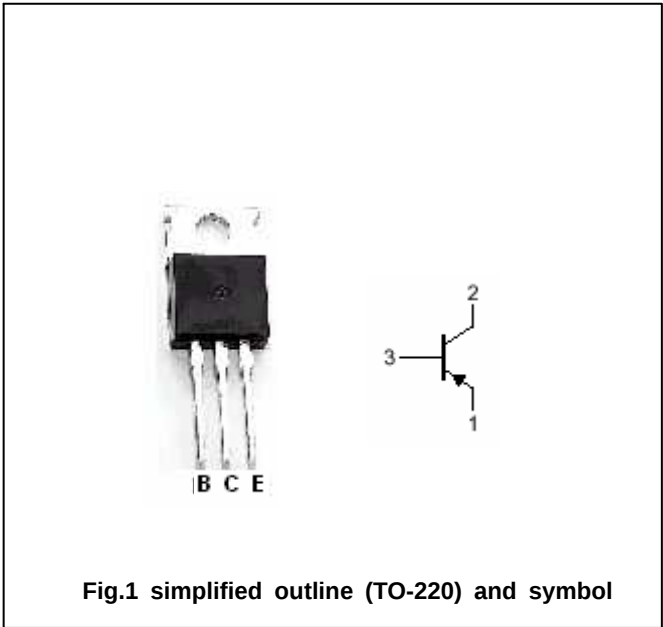


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA968	Open emitter	-160	V
		2SA968A		-180	
		2SA968B		-200	
V_{CEO}	Collector-emitter voltage	2SA968	Open base	-160	V
		2SA968A		-180	
		2SA968B		-200	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-1.5	A
I_E	Emitter current			1.5	A
P_T	Total power dissipation		$T_C=25$	25	W
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA968	I _C =-10mA; I _B =0	-160			V
		2SA968A		-180			
		2SA968B		-200			
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =-1mA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage		I _C =-0.5A; I _B =-50mA			-1.5	V
V _{BE}	Base-emitter on voltage		I _C =-500mA ; V _{CE} =-5V			-1.0	V
I _{CBO}	Collector cut-off current		V _{CB} =-160V ; I _E =0			-1.0	μ A
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-1.0	μ A
h _{FE}	DC current gain		I _C =-100mA ; V _{CE} =-5V	70		240	
C _{ob}	Output capacitance		I _E =0 ; V _{CB} =-10V,f=1MHz		30		pF
f _T	Transition frequency		I _C =-100mA ; V _{CE} =10V		100		MHz

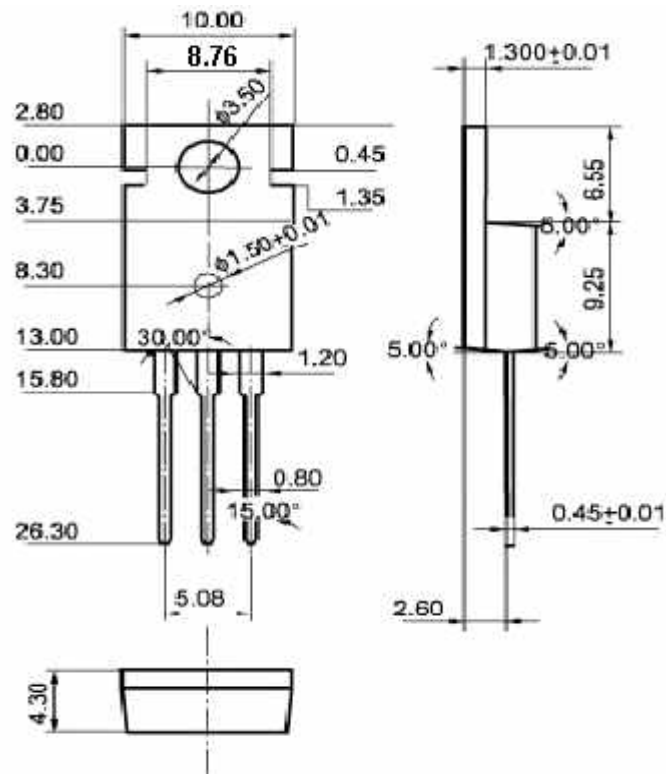
◆ h_{FE} Classifications

O	Y
70-140	120-240

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PACKAGE OUTLINE

Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)